

# BC857BTT1G

## General Purpose Transistor

### PNP Silicon

These transistors are designed for general purpose amplifier applications. They are housed in the SOT-416/SC-75 which is designed for low power surface mount applications.

#### Features

- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- This is a Pb-Free Device

#### MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ )

Rating	Symbol	Max	Unit
Collector-Emitter Voltage	$V_{CEO}$	-45	V
Collector-Base Voltage	$V_{CBO}$	-50	V
Emitter-Base Voltage	$V_{EBO}$	-5.0	V
Collector Current – Continuous	$I_C$	-100	mAdc
Collector Current – Peak	$I_C$	-200	mAdc

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation, FR-4 Board (Note 1) $T_A = 25^\circ\text{C}$ Derated above $25^\circ\text{C}$	$P_D$	200 1.6	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{\theta JA}$	600	$^\circ\text{C/W}$
Total Device Dissipation, FR-4 Board (Note 2) $T_A = 25^\circ\text{C}$ Derated above $25^\circ\text{C}$	$P_D$	300 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	400	$^\circ\text{C/W}$
Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

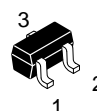
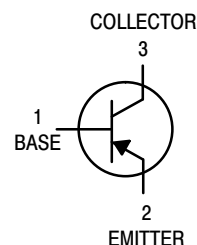
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR-4 @ min pad.
2. FR-4 @  $1.0 \times 1.0$  in pad.



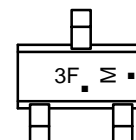
ON Semiconductor®

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CASE 463  
SOT-416  
STYLE 1

#### MARKING DIAGRAM



3F = Device Code  
M = Date Code  
■ = Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation may vary depending upon manufacturing location.

#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

# BC857BTT1G

## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>					
Collector–Emitter Breakdown Voltage ( $I_C = -10\text{ mA}$ )	$V_{(BR)CEO}$	-45	–	–	V
Collector–Emitter Breakdown Voltage ( $I_C = -10\text{ }\mu\text{A}$ , $V_{EB} = 0$ )	$V_{(BR)CES}$	-50	–	–	V
Collector–Base Breakdown Voltage ( $I_C = -10\text{ }\mu\text{A}$ )	$V_{(BR)CBO}$	-50	–	–	V
Emitter–Base Breakdown Voltage ( $I_E = -1.0\text{ }\mu\text{A}$ )	$V_{(BR)EBO}$	-5.0	–	–	V
Collector Cutoff Current ( $V_{CB} = -30\text{ V}$ ) ( $V_{CB} = -30\text{ V}$ , $T_A = 150^\circ\text{C}$ )	$I_{CBO}$	–	–	-15 -4.0	nA $\mu\text{A}$
<b>ON CHARACTERISTICS</b>					
DC Current Gain ( $I_C = -10\text{ }\mu\text{A}$ , $V_{CE} = -5.0\text{ V}$ ) ( $I_C = -2.0\text{ mA}$ , $V_{CE} = -5.0\text{ V}$ )	$h_{FE}$	– 220	150 290	– 475	–
Collector–Emitter Saturation Voltage ( $I_C = -10\text{ mA}$ , $I_B = -0.5\text{ mA}$ ) ( $I_C = -100\text{ mA}$ , $I_B = -5.0\text{ mA}$ )	$V_{CE(sat)}$	– –	– –	-0.3 -0.65	V
Base–Emitter Saturation Voltage ( $I_C = -10\text{ mA}$ , $I_B = -0.5\text{ mA}$ ) ( $I_C = -100\text{ mA}$ , $I_B = -5.0\text{ mA}$ )	$V_{BE(sat)}$	– –	-0.7 -0.9	– –	V
Base–Emitter On Voltage ( $I_C = -2.0\text{ mA}$ , $V_{CE} = -5.0\text{ V}$ ) ( $I_C = -10\text{ mA}$ , $V_{CE} = -5.0\text{ V}$ )	$V_{BE(on)}$	-0.6 –	– –	-0.75 -0.82	V
<b>SMALL–SIGNAL CHARACTERISTICS</b>					
Current–Gain – Bandwidth Product ( $I_C = -10\text{ mA}$ , $V_{CE} = -5.0\text{ Vdc}$ , $f = 100\text{ MHz}$ )	$f_T$	100	–	–	MHz
Output Capacitance ( $V_{CB} = -10\text{ V}$ , $f = 1.0\text{ MHz}$ )	$C_{ob}$	–	–	4.5	pF
Noise Figure ( $I_C = -0.2\text{ mA}$ , $V_{CE} = -5.0\text{ Vdc}$ , $R_S = 2.0\text{ k}\Omega$ , $f = 1.0\text{ kHz}$ , $BW = 200\text{ Hz}$ )	NF	–	–	10	dB

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS

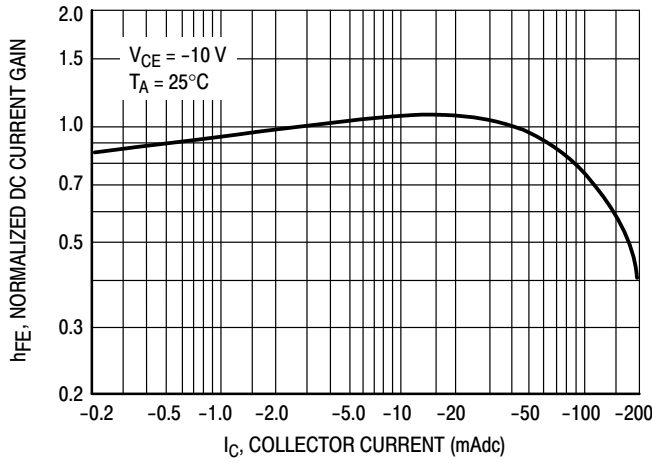


Figure 1. Normalized DC Current Gain

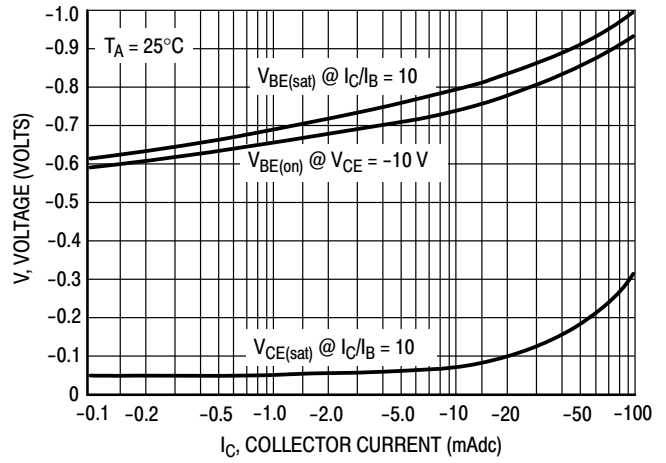


Figure 2. "Saturation" and "On" Voltages

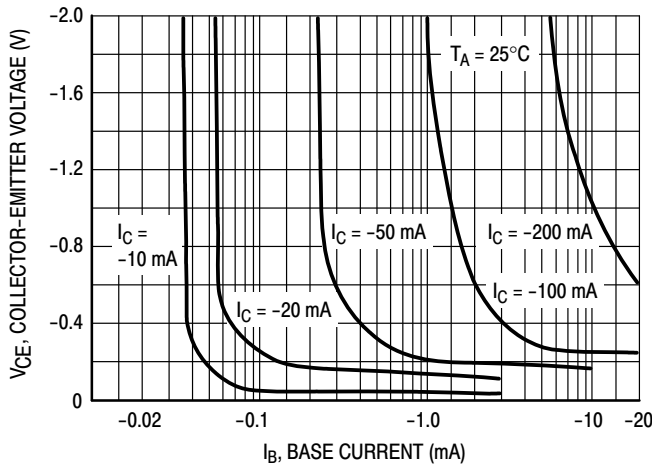


Figure 3. Collector Saturation Region

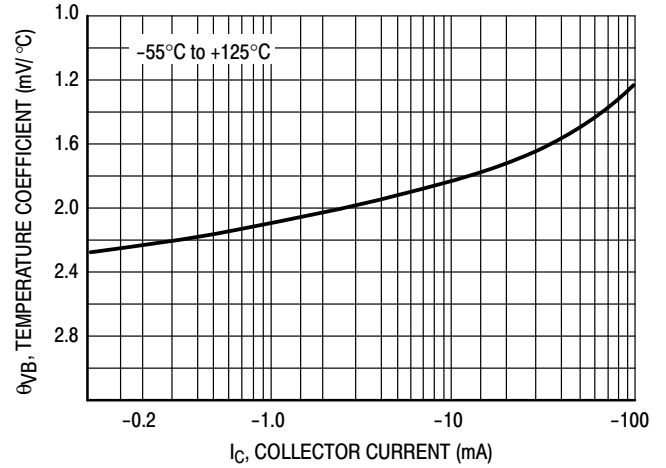


Figure 4. Base-Emitter Temperature Coefficient

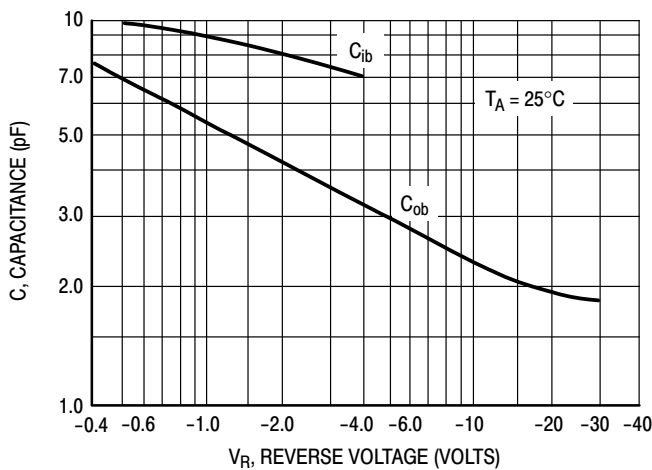


Figure 5. Capacitances

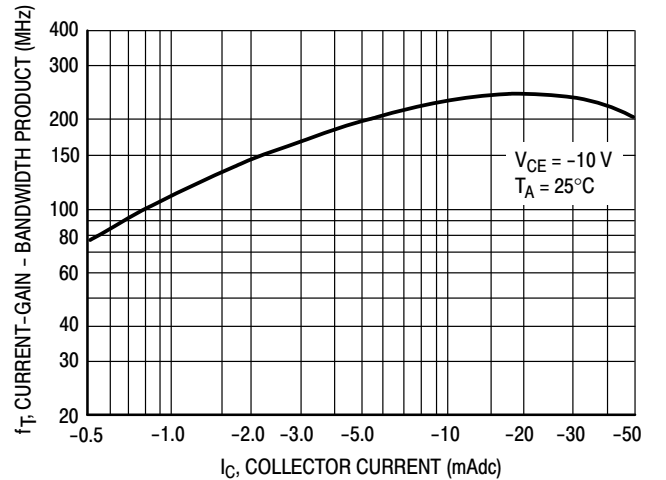


Figure 6. Current-Gain - Bandwidth Product

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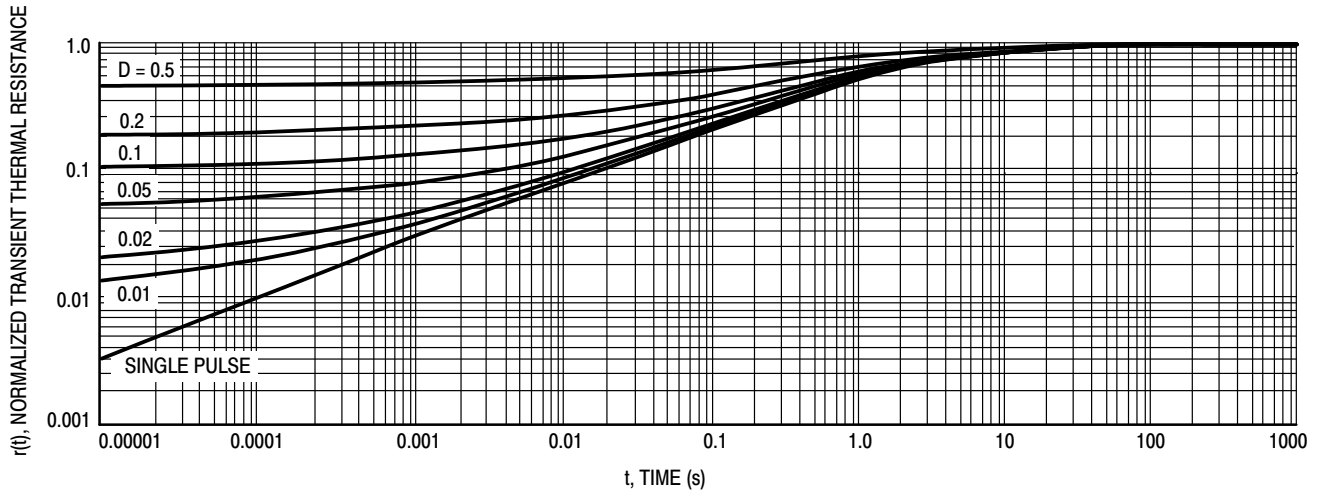


Figure 7. Thermal Response

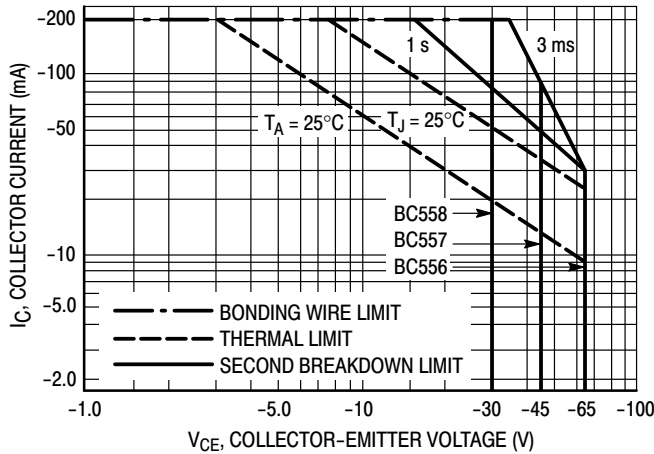


Figure 8. Active Region Safe Operating Area

The safe operating area curves indicate  $I_C$ – $V_{CE}$  limits of the transistor that must be observed for reliable operation. Collector load lines for specific circuits must fall below the limits indicated by the applicable curve.

The data of Figure 8 is based upon  $T_{J(pk)} = 150^\circ\text{C}$ ;  $T_C$  or  $T_A$  is variable depending upon conditions. Pulse curves are valid for duty cycles to 10% provided  $T_{J(pk)} \leq 150^\circ\text{C}$ .  $T_{J(pk)}$  may be calculated from the data in Figure 7. At high case or ambient temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by the secondary breakdown.

## ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
BC857BTT1G	SOT-416 (PB-Free)	3,000 / Tape & Reel
NSVBC857BTT1G*		

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

\*NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

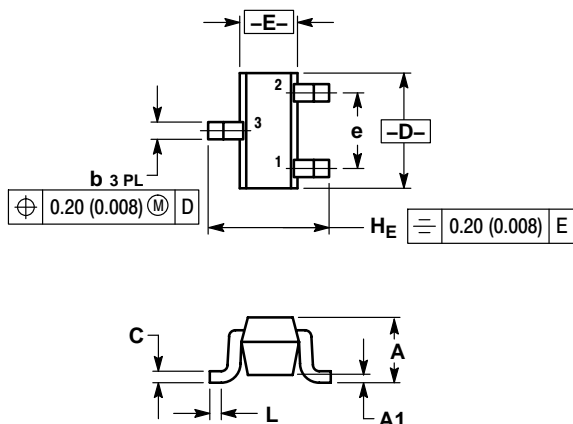
# BC857BTT1G

## PACKAGE DIMENSIONS

### SOT-416 (SC-75)

CASE 463

ISSUE F

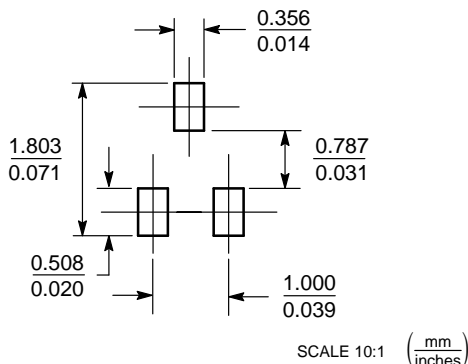


#### NOTES:


1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.70	0.80	0.90	0.027	0.031	0.035
A1	0.00	0.05	0.10	0.000	0.002	0.004
b	0.15	0.20	0.30	0.006	0.008	0.012
C	0.10	0.15	0.25	0.004	0.006	0.010
D	1.55	1.60	1.65	0.059	0.063	0.067
E	0.70	0.80	0.90	0.027	0.031	0.035
e	1.00 BSC			0.04 BSC		
L	0.10	0.15	0.20	0.004	0.006	0.008
H <sub>E</sub>	1.50	1.60	1.70	0.061	0.063	0.065

### SOLDERING FOOTPRINT\*



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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